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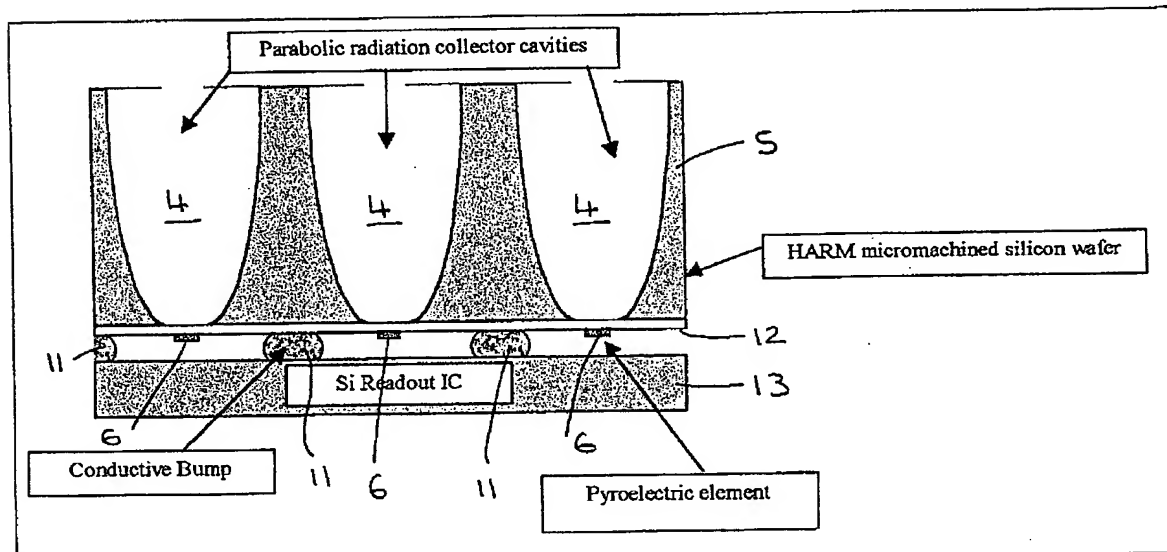
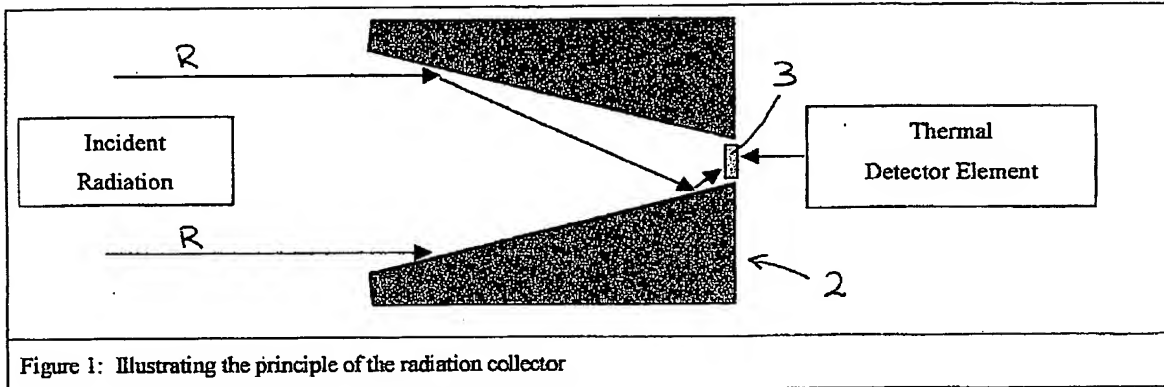


Figure 2a: Schematic diagram of the radiation collector structure envisaged.

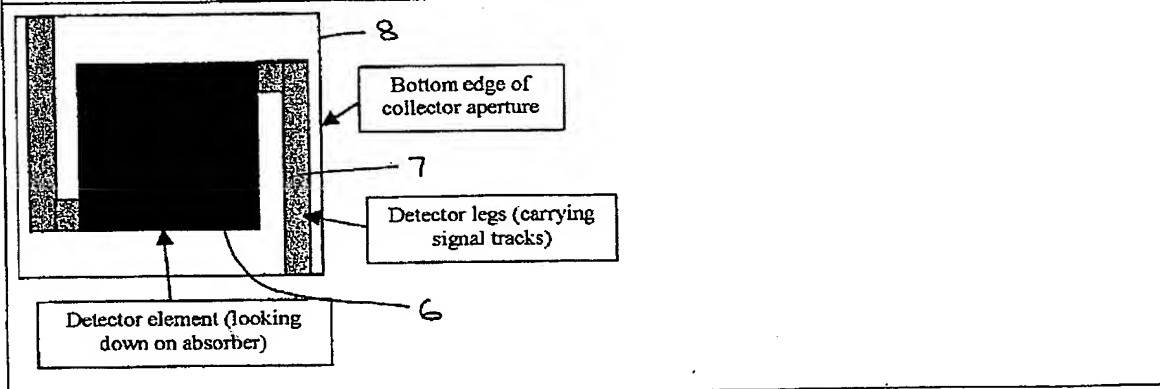
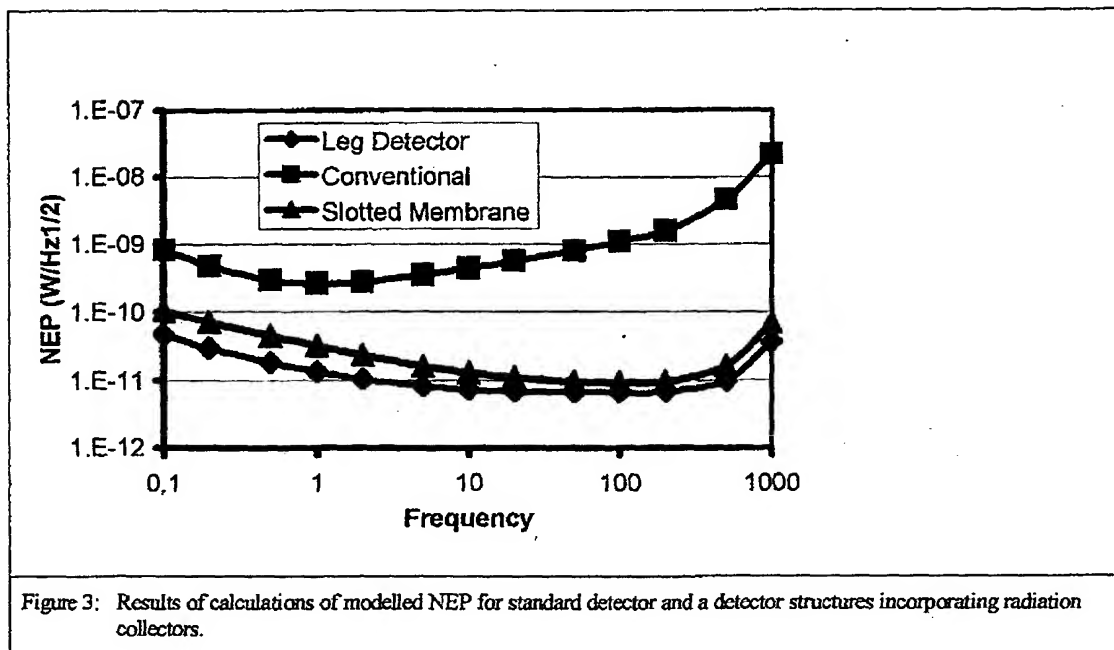
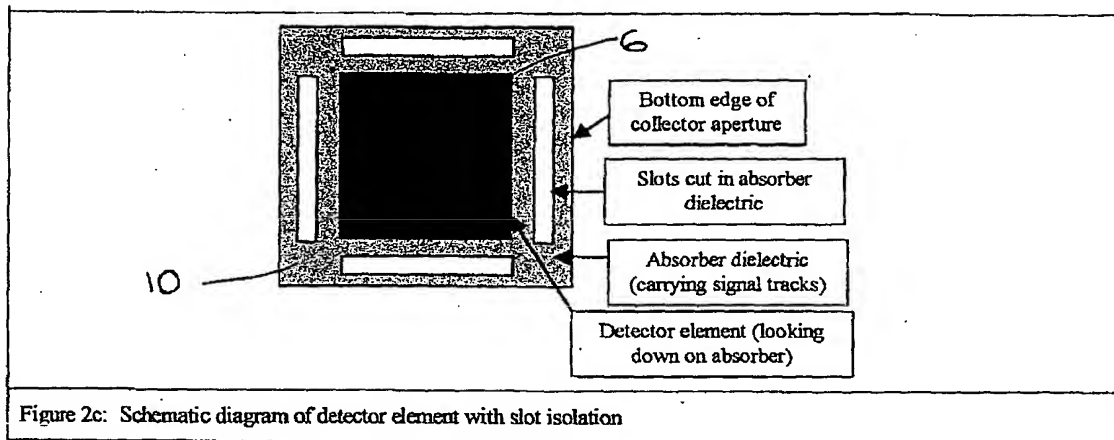


Figure 2b: Schematic diagram of detector element with leg isolation

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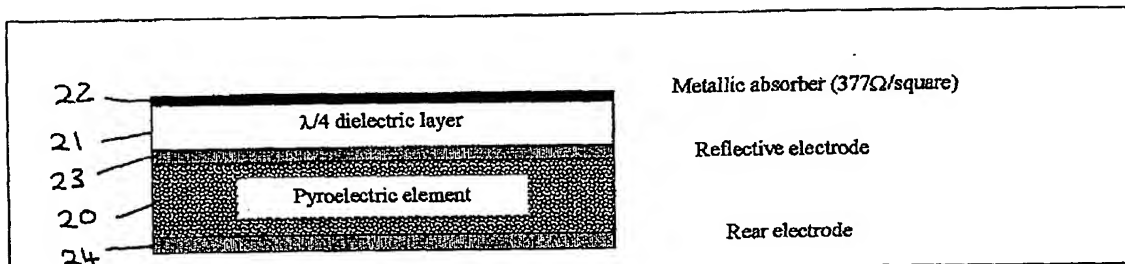


Figure 4a: Dielectric absorber layer (1.7μm SiO₂)

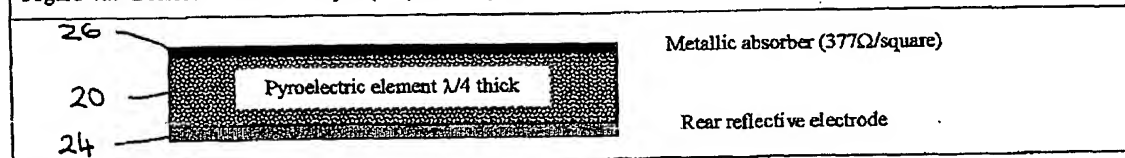


Figure 4b: Pyroelectric thin film as the absorber layer.

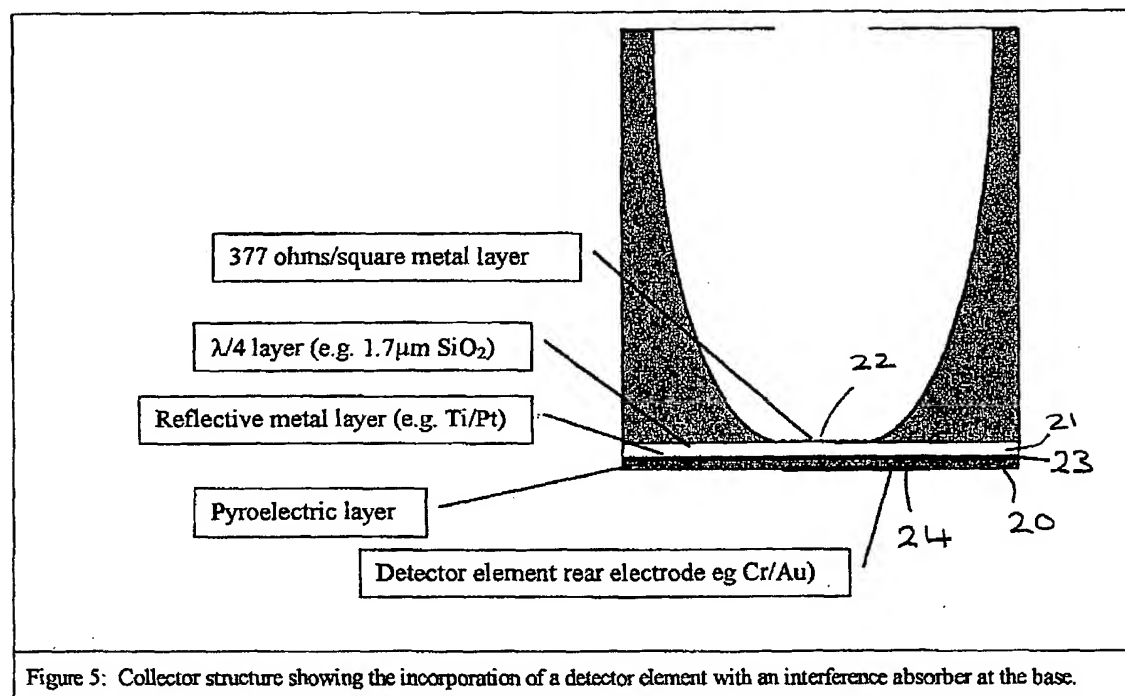
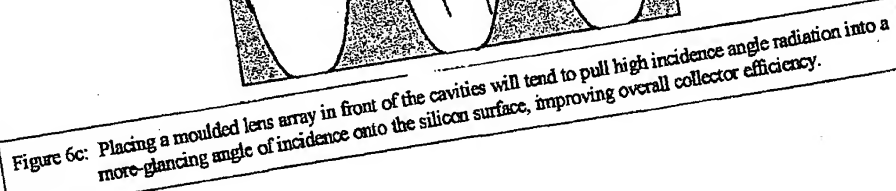
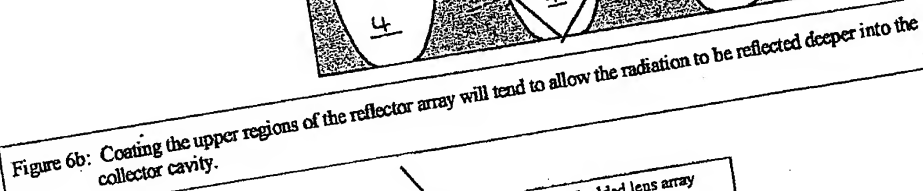
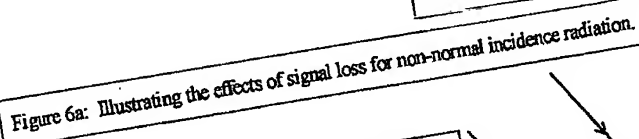


Figure 5: Collector structure showing the incorporation of a detector element with an interference absorber at the base.

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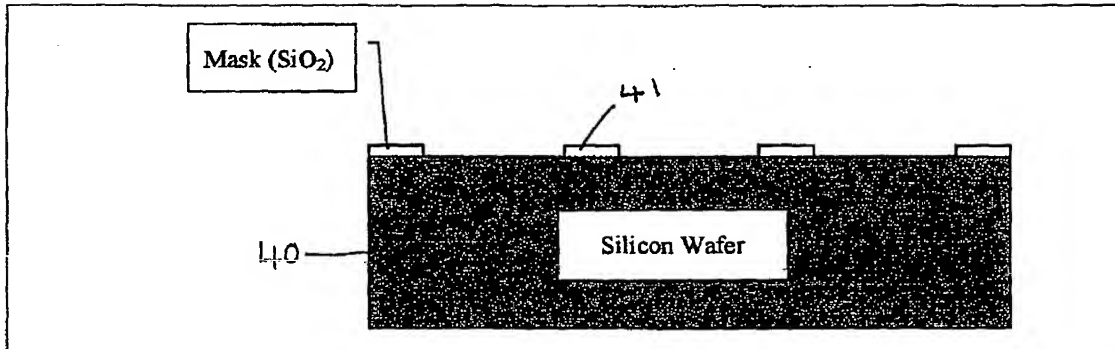


Figure 7a: Silicon wafer with "hard" mask defined

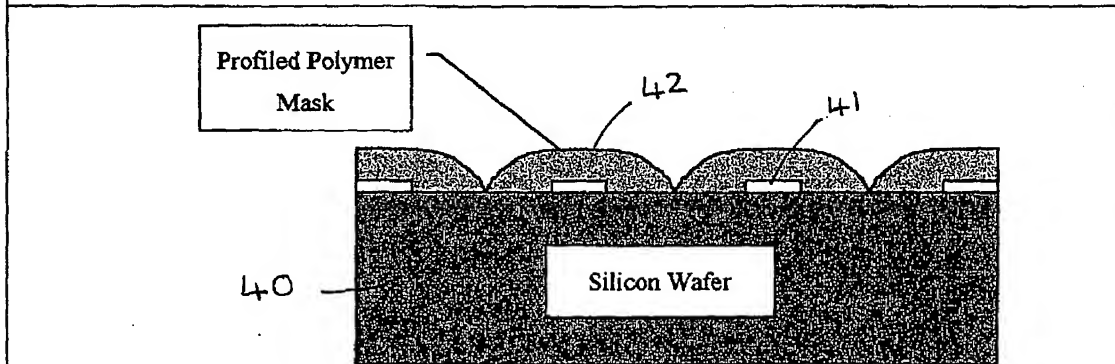


Figure 7b: Silicon wafer with profiled polymer mask defined

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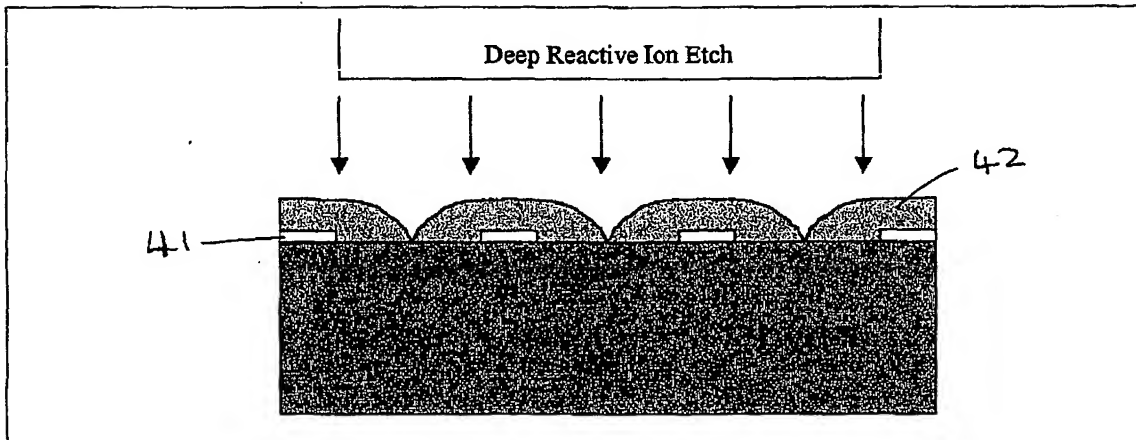


Figure 7c: Silicon wafer with masks exposed to DRIE

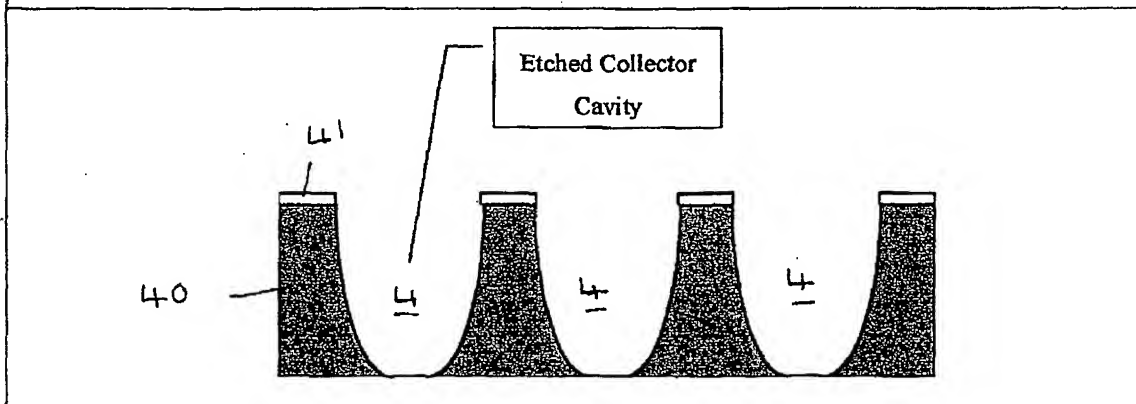


Figure 7d: Silicon wafer with cavities etched by DRIE

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